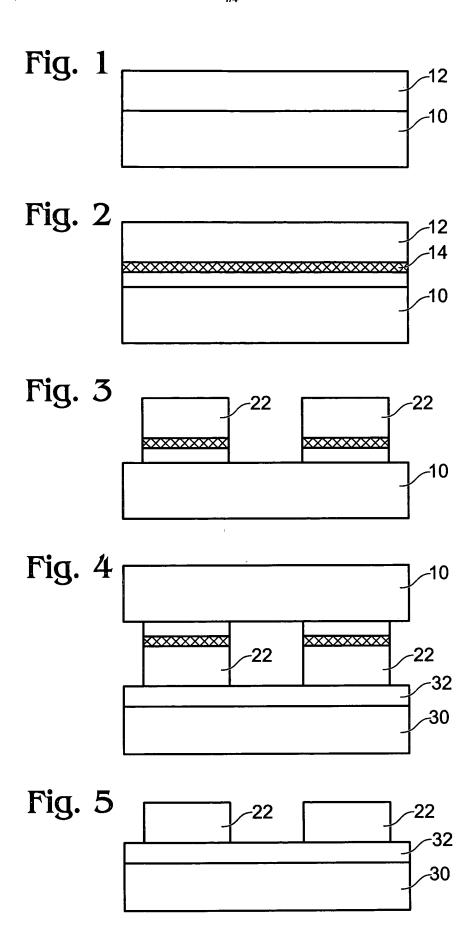
Method of Making Relaxed Silicon-Germanium on Insulator via Layer Transfer Serial No.: 10/665, 944 Jer-Shen Maa, Jong-Jan Lee, Douglas J. Tweet, and Sheng Teng Hsu



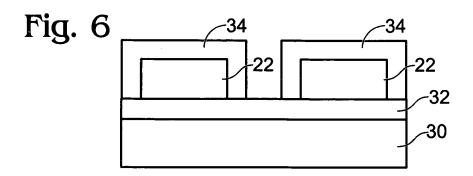
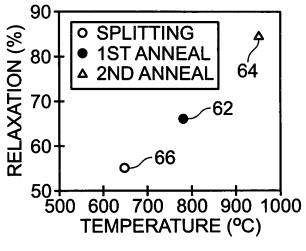
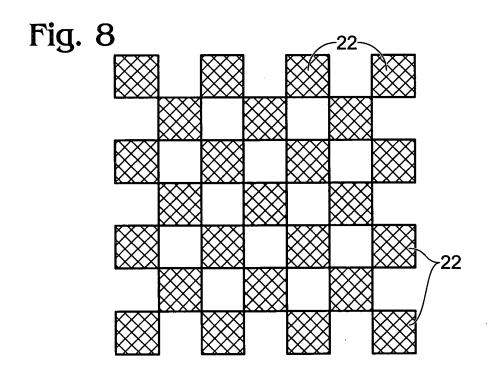
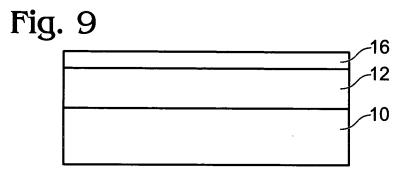
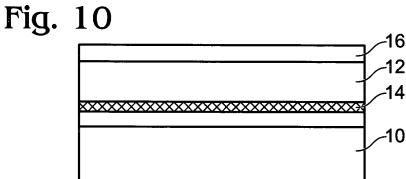


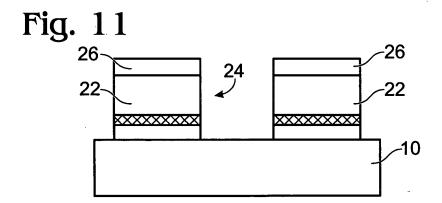
Fig. 7 RELAXATION OF SIGE ON SIO2 AFTER WAFER SPLITTING AND ANNEAL











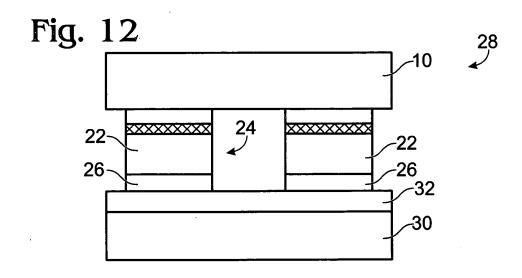


Fig. 13

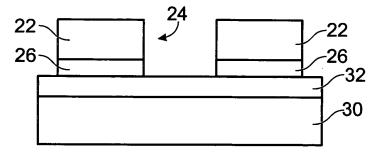


Fig. 14

